

isc N-Channel MOSFET Transistor

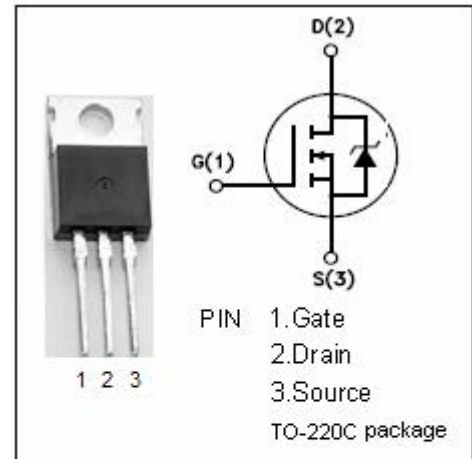
BUK454-800A/B

DESCRIPTION

- High speed switching
- Easy driver for cost effective application

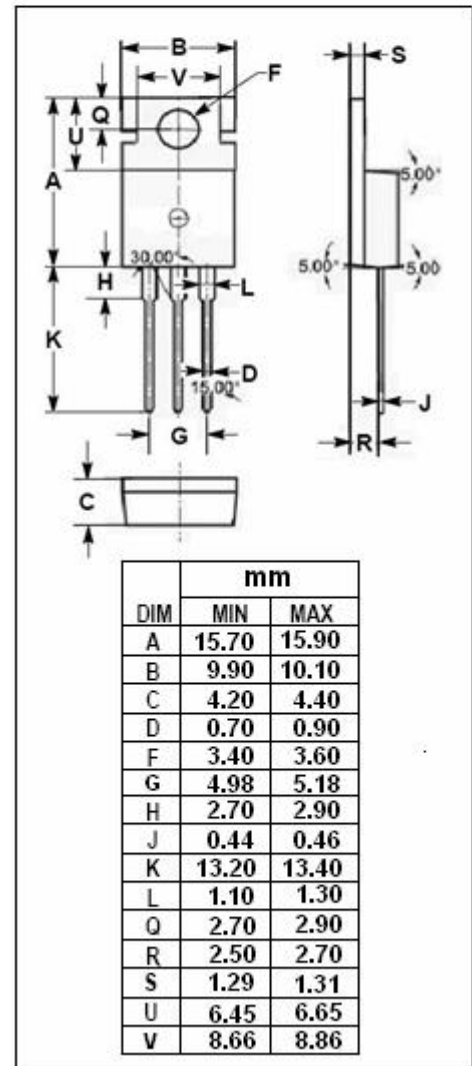
APPLICATIONS

- use in Switched Mode Power Supplies (SMPS), motor control, welding, And in general purpose switching resistance application



ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage (V _{GS} =0)	800	V
V _{GS}	Gate-Source Voltage	±30	V
I _D	Drain Current-continuous @ TC=37°C	BUK454-800A	2.6
		BUK454-800B	2.0
P _{tot}	Total Dissipation@TC=25°C	100	W
T _j	Max. Operating Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	150	°C



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance,Junction to Case	1.47	°C/W
R _{th j-a}	Thermal Resistance,Junction to Ambient	60	°C/W

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• ELECTRICAL CHARACTERISTICS (T_C=25°C)

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = 0.25mA	800		V
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D = 1mA	2.1	4	V
R _{DS(ON)}	Drain-Source On-stage Resistance	V _{GS} = 10V; I _D = 1A		6	Ω
				8	
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±30V; V _{DS} = 0		±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 800V; V _{GS} = 0		20	uA
V _{SD}	Diode Forward Voltage	I _F = 2.6A; V _{GS} = 0		1.3	V